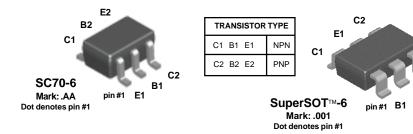


FFB2227A

FMB2227A



NPN & PNP General Purpose Amplifier

This complementary device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19 and 63. See FFB2222A (NPN) and FFB2907A (PNP) for characteristics.

Absolute Maximum Ratings* $T_{\Delta} = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics T_A = 25°C unless otherwise noted

Symbol	Characteristic	M	ax	Units	
		FFB2227A	FMB2227A		
P _D	Total Device Dissipation	300	700	mW	
	Derate above 25°C	2.4	5.6	mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	180	°C/W	

NPN & PNP General Purpose Amplifier (continued)

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T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
				I	I.	
OFF CHAF	RACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	30			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0			V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 50 \text{ V}, I_{E} = 0$			30	nA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$			30	nA
ON CHAR	ACTERISTICS					
h _{FE}	DC Current Gain	I _C = 1.0 mA, V _{CE} = 10 V I _C = 10 mA, V _{CE} = 10 V I _C = 150 mA, V _{CE} = 10 V*	50 75 100 30			
V _{CE(sat)}	Collector-Emitter Saturation Voltage*	$I_C = 300 \text{mA}, V_{CE} = 10 \text{ V}^*$ $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	30		0.4	V
JL(Sal)		$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$			1.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage*	I _C = 300 mA, I _B = 30 mA I _C = 150 mA, I _B = 15 mA			1.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage* GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 50 \text{ mA}, V_{CE} = 20 \text{ V},$		250		V V
V _{BE(sat)} SMALL SI	GNAL CHARACTERISTICS	I _C = 150 mA, I _B = 15 mA		250		V V MHz
$V_{BE(sat)}$ SMALL SI f_T C_{obo}	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 50 \text{ mA}, V_{CE} = 20 \text{ V},$ $f = 100 \text{ MHz}$				
V _{BE(sat)}	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 50$ mA, $V_{CE} = 20$ V, f = 100 MHz $V_{CB} = 10$ V, $I_E = 0$, $f = 100$ kHz		4.0		pF
V _{BE(sat)} SMALL SI f _T C _{obo} Cibo	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance	$\begin{split} I_C &= 150 \text{ mA}, \ I_B = 15 \text{ mA} \\ \\ I_C &= 50 \text{ mA}, \ V_{CE} = 20 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 10 \text{ V}, \ I_E = 0, \ f = 100 \text{ kHz} \\ \\ V_{EB} &= 2.0 \text{ V}, \ I_C = 0, \ f = 100 \text{ kHz} \\ \\ I_C &= 100 \text{ \muA}, \ V_{CE} = 10 \text{ V}, \end{split}$		4.0		pF
SMALL SI f _T C _{obo} C _{ibo} NF	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance Noise Figure	$\begin{split} I_C &= 150 \text{ mA}, \ I_B = 15 \text{ mA} \\ \\ I_C &= 50 \text{ mA}, \ V_{CE} = 20 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 10 \text{ V}, \ I_E = 0, \ f = 100 \text{ kHz} \\ \\ V_{EB} &= 2.0 \text{ V}, \ I_C = 0, \ f = 100 \text{ kHz} \\ \\ I_C &= 100 \text{ \muA}, \ V_{CE} = 10 \text{ V}, \end{split}$		4.0		pF pF
SMALL SI f _T Cobo Cibo NF SWITCHIN	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance Noise Figure NG CHARACTERISTICS	$\begin{split} I_C &= 150 \text{ mA}, \ I_B = 15 \text{ mA} \\ \\ I_C &= 50 \text{ mA}, \ V_{CE} = 20 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 10 \text{ V}, \ I_E = 0, \ f = 100 \text{ kHz} \\ \\ V_{EB} &= 2.0 \text{ V}, \ I_C = 0, \ f = 100 \text{ kHz} \\ \\ I_C &= 100 \mu\text{A}, \ V_{CE} = 10 \text{ V}, \\ R_S &= 1.0 k\Omega, \ f = 1.0 \text{ kHz} \end{split}$		4.0 12 2.0		pF pF dB
SMALL SI fr Cobo Cibo NF SWITCHIN	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance Noise Figure NG CHARACTERISTICS Turn-on Time	$\begin{split} I_C &= 150 \text{ mA}, \ I_B = 15 \text{ mA} \\ \\ I_C &= 50 \text{ mA}, \ V_{CE} = 20 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 10 \text{ V}, \ I_E = 0, \ f = 100 \text{ kHz} \\ \\ V_{EB} &= 2.0 \text{ V}, \ I_C = 0, \ f = 100 \text{ kHz} \\ \\ I_C &= 100 \mu\text{A}, \ V_{CE} = 10 \text{ V}, \\ \\ R_S &= 1.0 k\Omega, \ f = 1.0 \text{ kHz} \\ \\ \\ V_{CC} &= 30 \text{ V}, \ I_C = 150 \text{ mA}, \end{split}$		4.0 12 2.0		pF pF dB
SMALL SI fT Cobo Cibo NF SWITCHIN ton td	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance Noise Figure NG CHARACTERISTICS Turn-on Time Delay Time	$\begin{split} I_C &= 150 \text{ mA}, \ I_B = 15 \text{ mA} \\ \\ I_C &= 50 \text{ mA}, \ V_{CE} = 20 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 10 \text{ V}, \ I_E = 0, \ f = 100 \text{ kHz} \\ \\ V_{EB} &= 2.0 \text{ V}, \ I_C = 0, \ f = 100 \text{ kHz} \\ \\ I_C &= 100 \mu\text{A}, \ V_{CE} = 10 \text{ V}, \\ \\ R_S &= 1.0 k\Omega, \ f = 1.0 \text{ kHz} \\ \\ \\ V_{CC} &= 30 \text{ V}, \ I_C = 150 \text{ mA}, \end{split}$		4.0 12 2.0 30 8.0		pF pF dB
V _{BE(sat)} SMALL SI f _T C _{obo} Cibo	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance Noise Figure NG CHARACTERISTICS Turn-on Time Delay Time Rise Time	$\begin{split} &I_C = 150 \text{ mA}, \ I_B = 15 \text{ mA} \\ &I_C = 50 \text{ mA}, \ V_{CE} = 20 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CB} = 10 \text{ V}, \ I_E = 0, \ f = 100 \text{ kHz} \\ &V_{EB} = 2.0 \text{ V}, \ I_C = 0, \ f = 100 \text{ kHz} \\ &I_C = 100 \ \mu\text{A}, \ V_{CE} = 10 \text{ V}, \\ &R_S = 1.0 \ k\Omega, \ f = 1.0 \text{ kHz} \\ \end{split}$		30 8.0 20		pF pF dB ns ns ns

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

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